

# IRF7821PbF

HEXFET® Power MOSFET

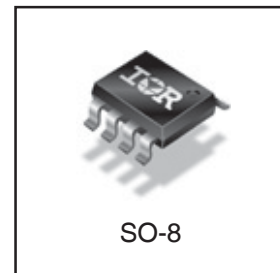
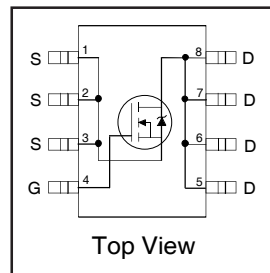
## Applications

- High Frequency Point-of-Load Synchronous Buck Converter for Applications in Networking & Computing Systems.
- Lead-Free

## Benefits

- Very Low  $R_{DS(on)}$  at 4.5V  $V_{GS}$
- Low Gate Charge
- Fully Characterized Avalanche Voltage and Current

$V_{DSS}$	$R_{DS(on)}$ max	$Q_g$ (typ.)
30V	9.1m $\Omega$ @ $V_{GS}=10V$	9.3nC



## Absolute Maximum Ratings

	Parameter	Max.	Units
$V_{DS}$	Drain-to-Source Voltage	30	V
$V_{GS}$	Gate-to-Source Voltage	$\pm 20$	
$I_D @ T_A = 25^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 10V$	13.6	A
$I_D @ T_A = 70^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 10V$	11	
$I_{DM}$	Pulsed Drain Current ①	100	
$P_D @ T_A = 25^\circ\text{C}$	Power Dissipation ④	2.5	W
$P_D @ T_A = 70^\circ\text{C}$	Power Dissipation ④	1.6	
	Linear Derating Factor	0.02	W/ $^\circ\text{C}$
$T_J$	Operating Junction and	-55 to + 155	$^\circ\text{C}$
$T_{STG}$	Storage Temperature Range		

## Thermal Resistance

	Parameter	Typ.	Max.	Units
$R_{\theta JL}$	Junction-to-Drain Lead ⑤	—	20	$^\circ\text{C}/\text{W}$
$R_{\theta JA}$	Junction-to-Ambient ④⑤	—	50	

Notes ① through ⑤ are on page 10

## Static @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$BV_{DSS}$	Drain-to-Source Breakdown Voltage	30	—	—	V	$V_{GS} = 0V, I_D = 250\mu A$
$\Delta BV_{DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	—	0.025	—	V/°C	Reference to $25^\circ\text{C}, I_D = 1mA$
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	—	7.0	9.1	mΩ	$V_{GS} = 10V, I_D = 13A$ ③
		—	9.5	12.5		$V_{GS} = 4.5V, I_D = 10A$ ③
$V_{GS(th)}$	Gate Threshold Voltage	1.0	—	—	V	$V_{DS} = V_{GS}, I_D = 250\mu A$
$\Delta V_{GS(th)}$	Gate Threshold Voltage Coefficient	—	-4.9	—	mV/°C	
$I_{DSS}$	Drain-to-Source Leakage Current	—	—	1.0	μA	$V_{DS} = 24V, V_{GS} = 0V$
		—	—	150		$V_{DS} = 24V, V_{GS} = 0V, T_J = 125^\circ\text{C}$
$I_{GSS}$	Gate-to-Source Forward Leakage	—	—	100	nA	$V_{GS} = 20V$
	Gate-to-Source Reverse Leakage	—	—	-100		$V_{GS} = -20V$
$g_{fs}$	Forward Transconductance	22	—	—	S	$V_{DS} = 15V, I_D = 10A$
$Q_g$	Total Gate Charge	—	9.3	14	nC	$V_{DS} = 15V$ $V_{GS} = 4.5V$ $I_D = 10A$ See Fig. 16
$Q_{gs1}$	Pre-V <sub>th</sub> Gate-to-Source Charge	—	2.5	—		
$Q_{gs2}$	Post-V <sub>th</sub> Gate-to-Source Charge	—	0.8	—		
$Q_{gd}$	Gate-to-Drain Charge	—	2.9	—		
$Q_{godr}$	Gate Charge Overdrive	—	3.1	—		
$Q_{sw}$	Switch Charge ( $Q_{gs2} + Q_{gd}$ )	—	3.7	—		
$Q_{oss}$	Output Charge	—	6.1	—	nC	$V_{DS} = 10V, V_{GS} = 0V$
$t_{d(on)}$	Turn-On Delay Time	—	6.3	—	ns	$V_{DD} = 15V, V_{GS} = 4.5V$ ③ $I_D = 10A$ Clamped Inductive Load
$t_r$	Rise Time	—	2.7	—		
$t_{d(off)}$	Turn-Off Delay Time	—	9.7	—		
$t_f$	Fall Time	—	7.3	—		
$C_{iss}$	Input Capacitance	—	1010	—	pF	$V_{GS} = 0V$
$C_{oss}$	Output Capacitance	—	360	—		$V_{DS} = 15V$
$C_{rss}$	Reverse Transfer Capacitance	—	110	—		$f = 1.0MHz$

## Avalanche Characteristics

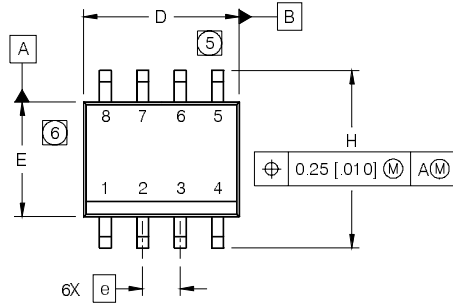
	Parameter	Typ.	Max.	Units
$E_{AS}$	Single Pulse Avalanche Energy ②⑥	—	44	mJ
$I_{AR}$	Avalanche Current ①	—	10	A

## Diode Characteristics

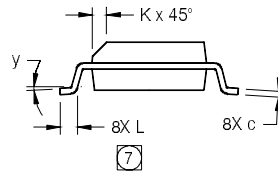
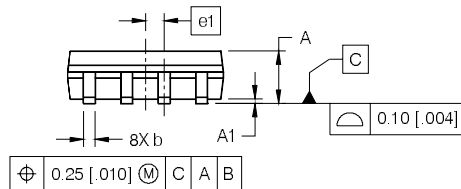
	Parameter	Min.	Typ.	Max.	Units	Conditions
$I_S$	Continuous Source Current (Body Diode)	—	—	3.1	A	MOSFET symbol showing the integral reverse p-n junction diode.
$I_{SM}$	Pulsed Source Current (Body Diode) ①⑥	—	—	100		
$V_{SD}$	Diode Forward Voltage	—	—	1.0	V	$T_J = 25^\circ\text{C}, I_S = 10A, V_{GS} = 0V$ ③
$t_{rr}$	Reverse Recovery Time	—	28	42	ns	$T_J = 25^\circ\text{C}, I_F = 10A, V_{DD} = 20V$
$Q_{rr}$	Reverse Recovery Charge	—	23	35	nC	$di/dt = 100A/\mu s$ ③

## SO-8 Package Details

Dimensions are shown in millimeters (inches)



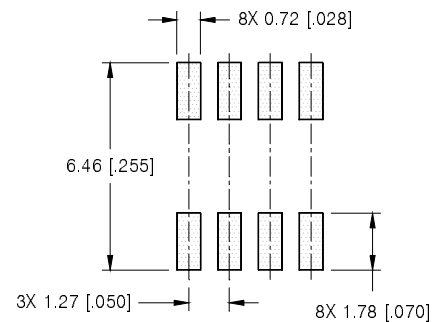
DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.0532	.0688	1.35	1.75
A1	.0040	.0098	0.10	0.25
b	.013	.020	0.33	0.51
c	.0075	.0098	0.19	0.25
D	.189	.1968	4.80	5.00
E	.1497	.1574	3.80	4.00
e	.050 BASIC		1.27 BASIC	
e1	.025 BASIC		0.635 BASIC	
H	.2284	.2440	5.80	6.20
K	.0099	.0196	0.25	0.50
L	.016	.050	0.40	1.27
y	0°	8°	0°	8°



### NOTES:

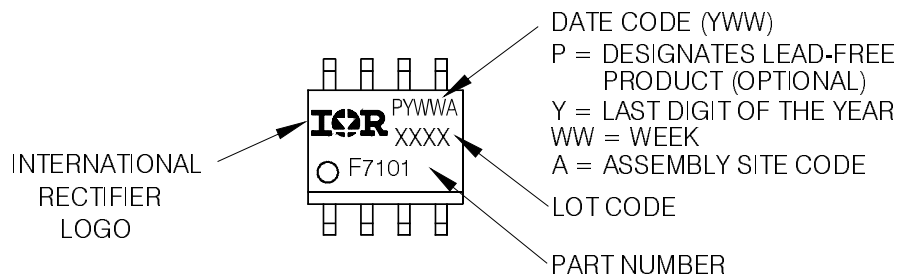
1. DIMENSIONING & TOLERANCING PER ASME Y14.5M-1994.
2. CONTROLLING DIMENSION: MILLIMETER
3. DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES].
4. OUTLINE CONFORMS TO JEDEC OUTLINE MS-012AA.
- 5 DIMENSION DOES NOT INCLUDE MOLD PROTRUSIONS. MOLD PROTRUSIONS NOT TO EXCEED 0.15 [.006].
- 6 DIMENSION DOES NOT INCLUDE MOLD PROTRUSIONS. MOLD PROTRUSIONS NOT TO EXCEED 0.25 [.010].
- 7 DIMENSION IS THE LENGTH OF LEAD FOR SOLDERING TO A SUBSTRATE.

### FOOTPRINT



## SO-8 Part Marking

EXAMPLE: THIS IS AN IRF7101 (MOSFET)

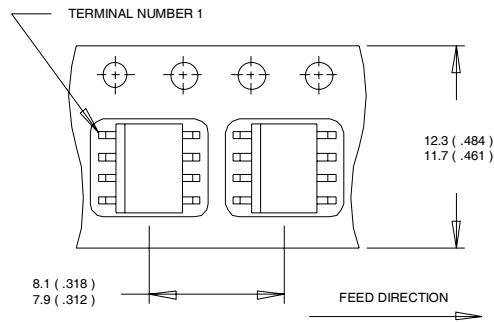


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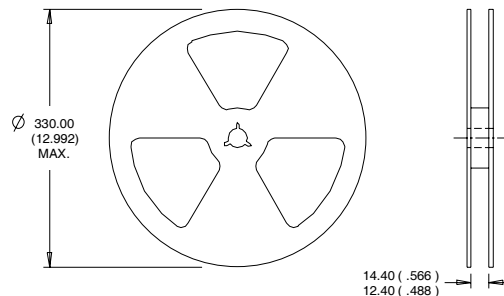
International  
**IOR** Rectifier

## SO-8 Tape and Reel

Dimensions are shown in millimeters (inches)



- NOTES:
1. CONTROLLING DIMENSION : MILLIMETER.
  2. ALL DIMENSIONS ARE SHOWN IN MILLIMETERS(INCHES).
  3. OUTLINE CONFORMS TO EIA-481 & EIA-541.



- NOTES :
1. CONTROLLING DIMENSION : MILLIMETER.
  2. OUTLINE CONFORMS TO EIA-481 & EIA-541.

### Notes:

- ① Repetitive rating; pulse width limited by max. junction temperature.
- ② Starting  $T_J = 25^\circ\text{C}$ ,  $L = 0.87\text{mH}$   
 $R_G = 25\Omega$ ,  $I_{AS} = 10\text{A}$ .
- ③ Pulse width  $\leq 400\mu\text{s}$ ; duty cycle  $\leq 2\%$ .
- ④ When mounted on 1 inch square copper board
- ⑤  $R_\theta$  is measured at  $T_J$  approximately  $90^\circ\text{C}$

Data and specifications subject to change without notice.  
This product has been designed and qualified for the Consumer market.

International  
**IOR** Rectifier